



# P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ)		
- 60	0.060 at V <sub>GS</sub> = - 10 V	- 19	26		
- 60	$0.077 \text{ at V}_{GS} = -4.5 \text{ V}$	- 16.8	20		

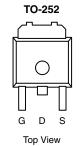
## **FEATURES**

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

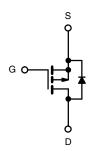


## **APPLICATIONS**

- · High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display



Drain Connected to Tab



P-Channel MOSFET

Ordering Information:	SUD19P06-60-E3	(Lead (Pb)-free)

SUD19P06-60-GE3 (Lead (Pb)-free and Halogen free)

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25$ °C, unless otherwise note)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 60	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I-	- 18.3		
Continuous Drain Current (1) = 130 °C)	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 8.19		
Pulsed Drain Current	I <sub>DM</sub>	- 30	Α		
Avalanche Current, Single Pulse		I <sub>AS</sub>	- 22	1	
Repetitive Avalanche Energy, Single Pulse <sup>a</sup> L = 0.1 mH		E <sub>AS</sub>	24.2	mJ	
Dower Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	38.5 <sup>c</sup>	w	
Power Dissipation	T <sub>A</sub> = 25 °C	] 'D	2.3 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marian and Lucation to Ambient	t ≤ 10 s	$R_{thJA}$	17	21	°C/W	
Maximum Junction-to-Ambient <sup>b</sup>	Steady State		45	55		
Maximum Junction-to-Case		$R_{thJC}$	2.7	3.25		

### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Based up on  $T_C = 25$  °C.

Document Number: 69253 S11-2132 Rev. B, 31-Oct-11



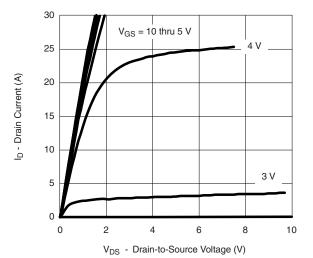
Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50		
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ} \text{ C}$			- 125		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 30			Α	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		0.048	0.060		
Drain Course On State Registered		$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}, T_J = 125 \text{ °C}$			0.102	Ω	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 150 °C			0.120		
		$V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$		0.061	0.077		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 10 A		22		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1140	1710	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		130			
Reverse Transfer Capacitance	C <sub>rss</sub>			90			
Total Gate Charge <sup>c</sup>	$Q_g$			26	40		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ A}$		4.5		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7		1	
Gate Resistance	Rg	f = 1 MHz		7		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V, R}_{L} = 3 \Omega$		9	15	ns ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -19 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		65	100		
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45		
Drain-Source Body Diode and Charact	eristics (T <sub>C</sub> = 2	5 °C) <sup>b</sup>		L			
Continuous Current	Is				- 30		
Pulsed Current	I <sub>SM</sub>				- 30	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 19 A, V <sub>GS</sub> = 0 V		- 1	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 19 A, di/dt = 100 A/μs		41	61	ns	

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

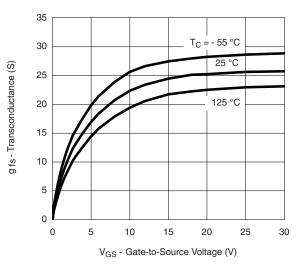
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



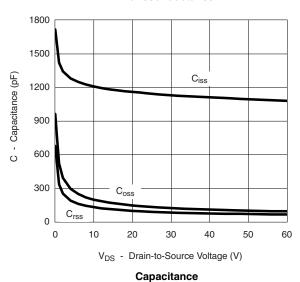
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

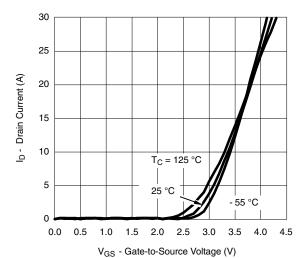


### **Output Characteristics**

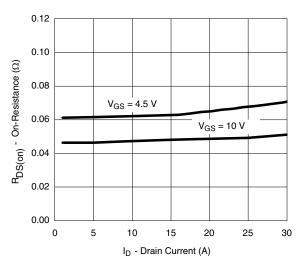


## **Transconductance**

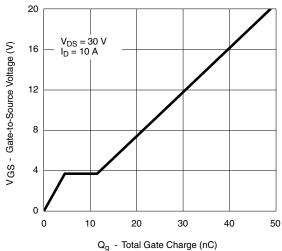




### **Transfer Characteristics**

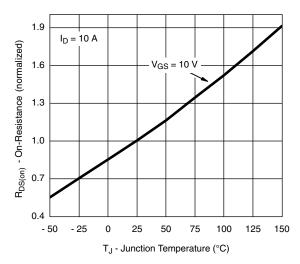


# On-Resistance vs. Drain Current

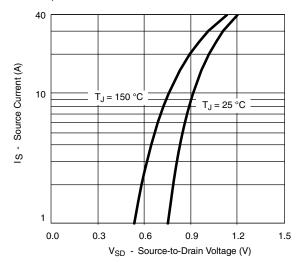


**Gate Charge** 

# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

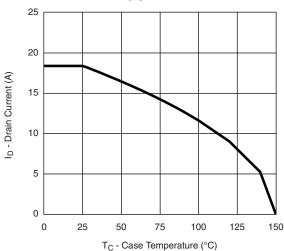


On-Resistance vs. Junction Temperature

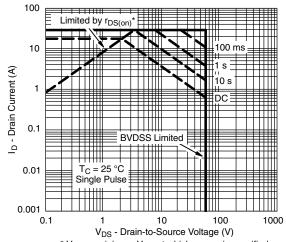


Source-Drain Diode Forward Voltage

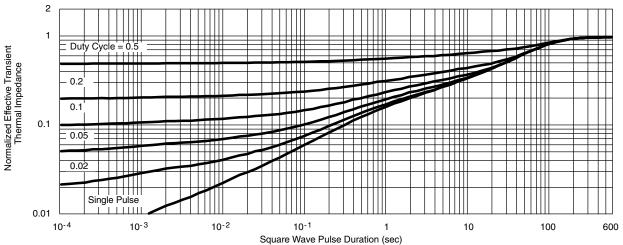
## THERMAL RATINGS



**Maximum Drain Current** vs. Case Temperature



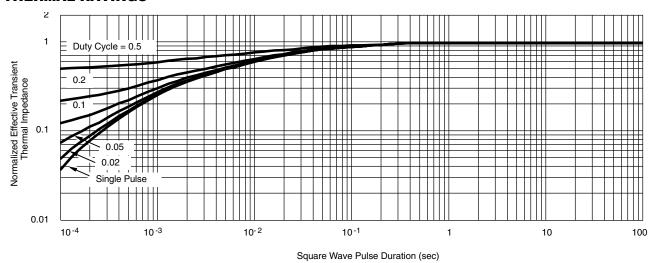
 $^{\star}$  V<sub>GS</sub> > minimum V<sub>GS</sub> at which  $r_{DS(on)}$  is specified Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS

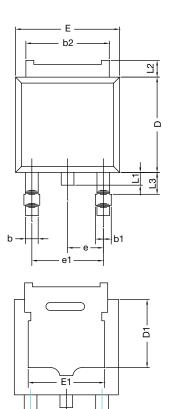


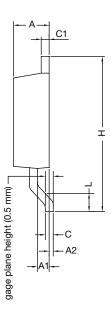
Normalized Thermal Transient Impedance, Junction-to-Case

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## **TO-252AA CASE OUTLINE**





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

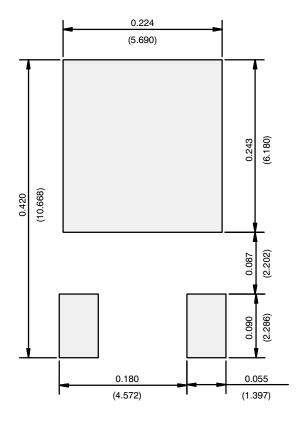
### Note

• Dimension L3 is for reference only.

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# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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